

LEGM75BH120L1H

IGBT Power Module

Features:

- $V_{CE}=1200V$ $I_C=75A$
- Low $V_{CE(sat)}$
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Isolation Type Package

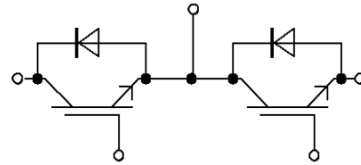
Applications:

- The inverter
- Motor control and drives

Package Type & Internal Circuit



L1



Internal Circuit

Maximum Rated Values (IGBT Inverter)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	$V_{EC}=0V, I_C=1mA, T_{vj}=25^\circ C$	1200	V
I_C	Continuous Collector Current	$T_C=100^\circ C$	75	A
I_{CRM}	Peak Collector Current	$I_{CRM}=2I_C$	150	A
V_{GES}	Gate-Emitter Voltage	$T_{vj}=25^\circ C$	± 30	V
P_{tot}	Total Power Dissipation	$T_C=25^\circ C, T_{vjmax}=150^\circ C$	350	W

Characteristics Values (IGBT Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=75\text{ A}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$		1.83	2.3	V	
		$I_C=75\text{ A}, V_{GE}=15\text{ V}, T_{vj}=150\text{ }^\circ\text{C}$		1.80		V	
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=5.0\text{ mA}, V_{CE}=V_{GE}, T_{vj}=25\text{ }^\circ\text{C}$	5.2	6.2	6.5	V	
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}=1200\text{ V}, V_{GE}=0\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$			20	μA	
I_{GES}	Gate-Emitter Leakage Current	$V_{CE}=0\text{ V}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$			200	nA	
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	$I_C = 75\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 2\ \Omega$ $T_{vj} = 25\text{ }^\circ\text{C}$		66		ns	
t_r	Rise Time, Inductive Load			35		ns	
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			270		ns	
t_f	Fall Time, Inductive Load			170		ns	
E_{on}	Turn-on Energy Loss per Pulse			2.3		mJ	
E_{off}	Energy Loss per Pulse			6.4		mJ	
$t_{d(on)}$	Turn-on Delay Time, Inductive Load				720		ns
t_r	Rise Time, Inductive Load				32		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load				335		ns
t_f	Fall Time, Inductive Load				276		ns
E_{on}	Turn-on Energy Loss per Pulse			2.7		mJ	
E_{off}	Energy Loss per Pulse			7.3		mJ	
R_{thJC}	Thermal resistance, junction to case	per IGBT			0.35	K/W	
$T_{vj\ op}$	Temperature under switching conditions		-40		150	$^\circ\text{C}$	
I_{SC}	SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 900\text{ V}$ $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$ $t_p \leq 10\ \mu\text{s}, T_{vj} = 150\text{ }^\circ\text{C}$		350		A	

Maximum Rated Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25\text{ }^{\circ}\text{C}$		1200		V
I_F	Continuous DC Forward Current	$T_C=100\text{ }^{\circ}\text{C}$		35		A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ ms}$		70		A
I^2t	I^2t Value	$V_R=0\text{ V}, t_p=10\text{ ms}, T_{vj}=150\text{ }^{\circ}\text{C}$		550		A^2s

Characteristic Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=30\text{ A}, V_{CE}=0\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$		1.9	2.2	V
		$I_F=30\text{ A}, V_{CE}=0\text{ V}, T_{vj}=150\text{ }^{\circ}\text{C}$		1.9	2.2	V
t_{rr}	Reverse Recovery time	$I_F=30\text{ A}, V_R=600\text{ V}$		350		ns
Q_r	Recovered Charge		$-di/dt=350\text{ A/us}$		2.3	μC
E_{rec}	Reverse Recovery Energy		$T_{vj}=25\text{ }^{\circ}\text{C}$		0.8	mJ
t_{rr}	Reverse Recovery time	$I_F=30\text{ A}, V_R=600\text{ V}$		620		ns
			Q_r	Recovered Charge	$-di/dt=350\text{ A/us}$	
E_{rec}	Reverse Recovery Energy		$T_{vj}=150\text{ }^{\circ}\text{C}$		1.25	mJ
R_{thJC}	Thermal resistance, junction to case	per Diode			0.83	K/W
$T_{vj\text{ op}}$	Operating Junction Temperature		-40		150	$^{\circ}\text{C}$

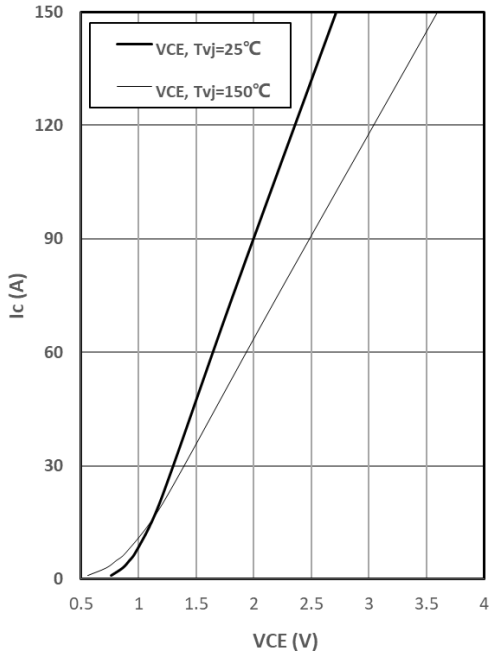
Module Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{isol}	Isolation voltage	$t=1\text{ min}, f=50\text{ Hz}$	2500			V
T_{stg}	Storage Temperature		-40		150	$^{\circ}\text{C}$
M_t	Module Electrodes Torque	Recommended(M5)	2.5		5.0	N·m
M_s	Module-to-Sink Torque	Recommended(M6)	3.0		6.0	N·m
G	Weight of Module			160		g

Output characteristic of IGBT, Inverter (typical)

$I_C = f(V_{CE})$

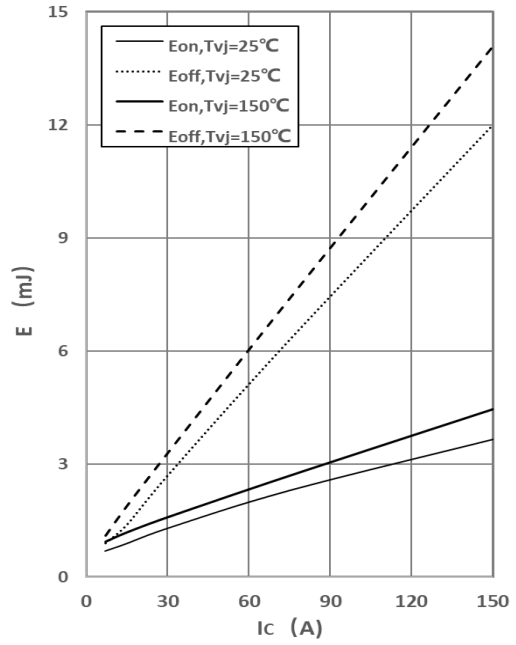
$V_{GE} = 15V$



Switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$

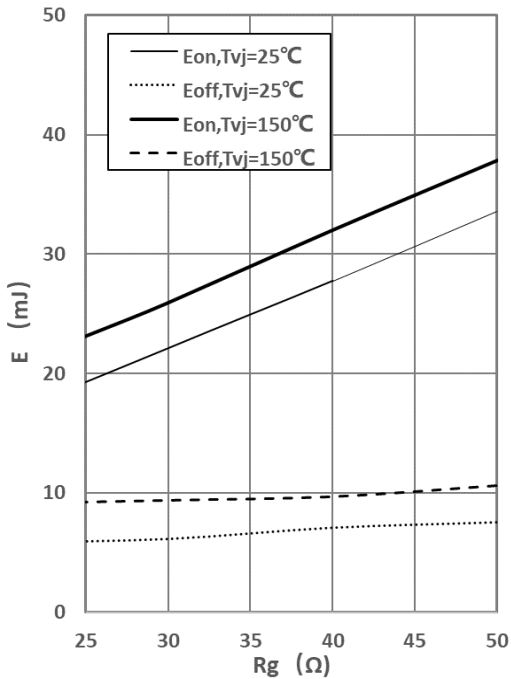
$V_{GE} = \pm 15V$, $R_G = 2\Omega$, $V_{CE} = 600V$



Switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$

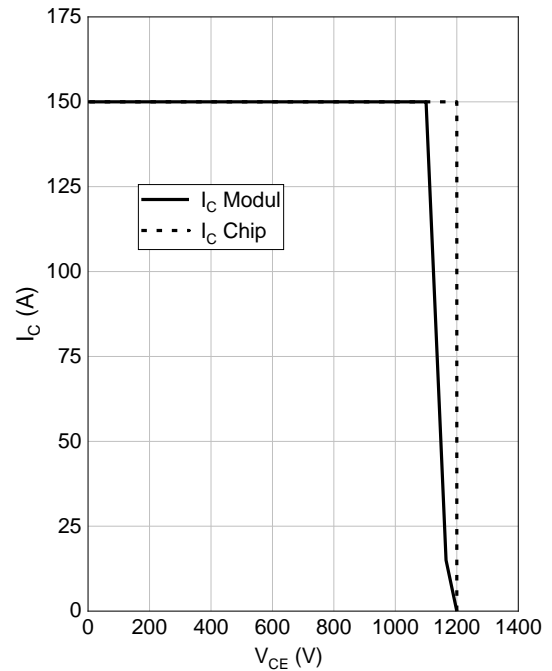
$V_{GE} = \pm 15V$, $I_C = 75A$, $V_{CE} = 600V$



RBSOA IGBT, Inverter (typical)

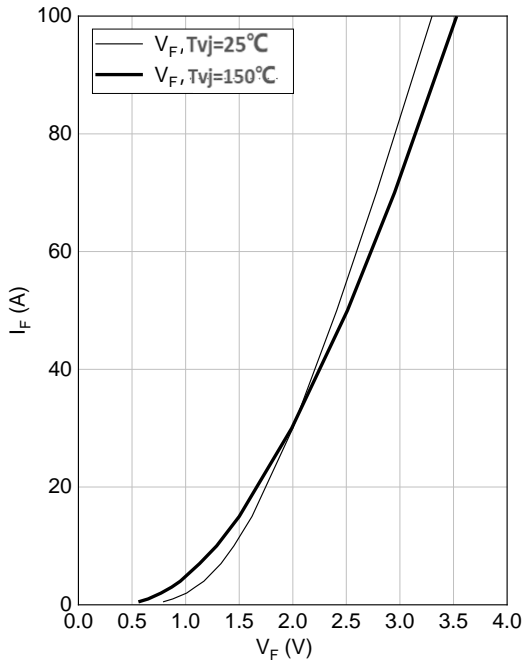
$I_C = f(V_{CE})$

$V_{GE} = \pm 15V$, $R_G = 2\Omega$, $T_{vj} = 150^\circ C$



Forward characteristic of Diode, Inverter (typical)

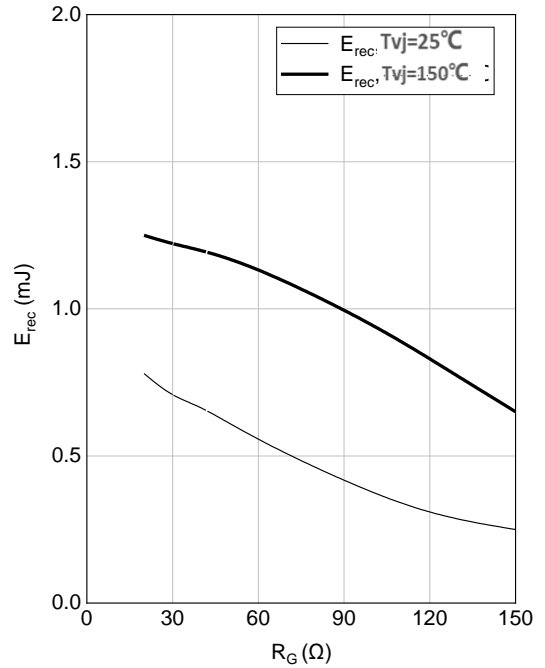
$$I_F = f(V_F)$$



Switching losses Diode, Inverter (typical)

$$E_{rec} = f(R_G)$$

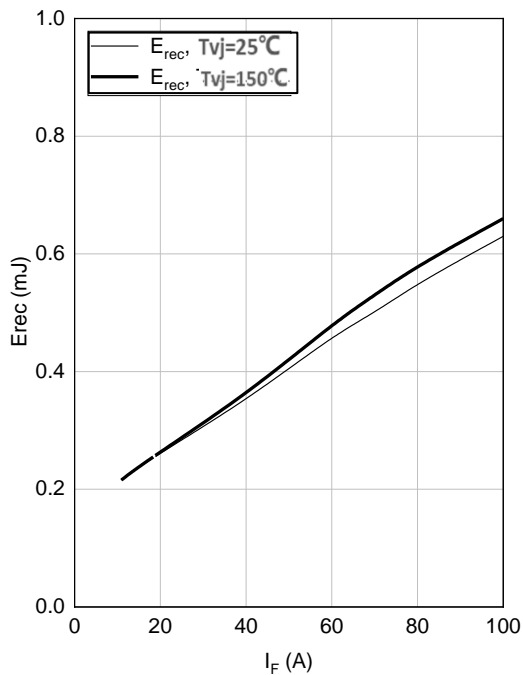
$$I_F = 75 \text{ A}, V_{CE} = 600 \text{ V}$$



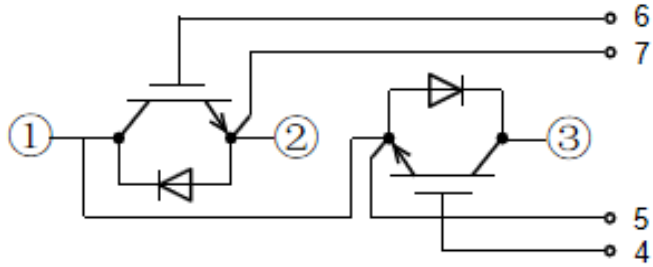
Switching losses Diode, Inverter (typical)

$$E_{rec} = f(I_F)$$

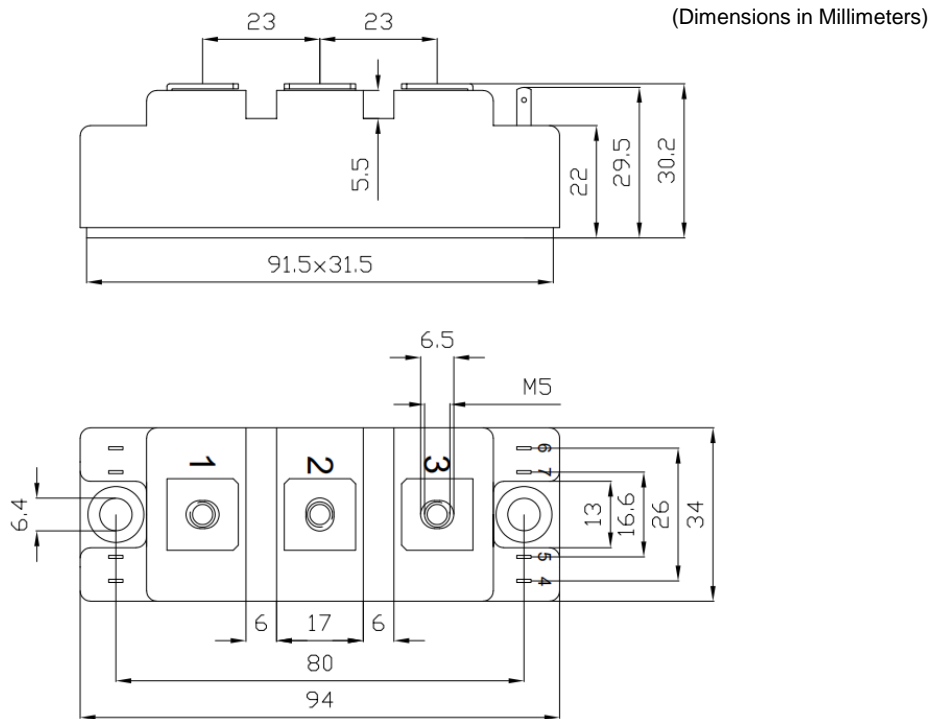
$$R_G = 2\Omega, V_{CE} = 600 \text{ V}$$



Circuit Diagram



Package Dimensions



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